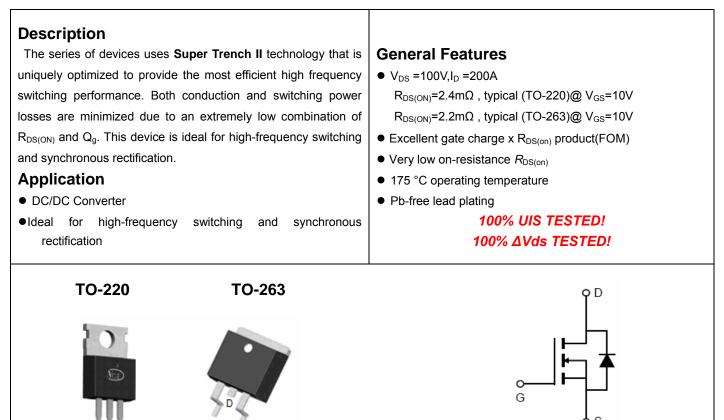


NCE N-Channel Super Trench II Power MOSFET



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP026N10	NCEP026N10	TO-220	-	-	-
NCEP026N10D	NCEP026N10D	TO-263	-	-	-

Absolute Maximum Ratings (T_c=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	VDS	100	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous	I _D	200	A	
Drain Current-Continuous(T _C =100 ℃)	I _D (100℃)	142	A	
Pulsed Drain Current	I _{DM}	800	A	
Maximum Power Dissipation	PD	300	W	
Derating factor		2	W/℃	
Single pulse avalanche energy (Note 5)	E _{AS}	2300	mJ	
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C	



0.5

R_{ejc}

Thermal Characteristic

Thermal Resistance, Junction-to-Case^(Note 2)

°C/W

Electrical Characteristics (T_C=25[°]C unless otherwise noted)

Parameter	Symbol	Condition		Min	Тур	Max	Unit
Off Characteristics	·					•	•
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V Ι _D =250μΑ		100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V		-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V		-	-	±100	nA
On Characteristics (Note 3)				•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$		2.0	3.0	4.0	V
Daria Orivera Ori Otata Dariatanan		V _{GS} =10V, I _D =100A	TO-220	-	2.4	2.6	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}		TO-263		2.2	2.6	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =100A			90	-	S
Dynamic Characteristics (Note4)				•			
Input Capacitance	C _{lss}	- V _{DS} =50V,V _{GS} =0V, F=1.0MHz		-	14000	-	PF
Output Capacitance	Coss			-	1100	-	PF
Reverse Transfer Capacitance	C _{rss}			-	60	-	PF
Switching Characteristics (Note 4)				•			
Turn-on Delay Time	t _{d(on)}			-	34	-	nS
Turn-on Rise Time	tr	V_{DD} =50V,I _D =100A V _{GS} =10V,R _G =1.6Ω		-	27	-	nS
Turn-Off Delay Time	t _{d(off)}			-	78	-	nS
Turn-Off Fall Time	t _f			-	30	-	nS
Total Gate Charge	Qg) (-	240	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =50V,I _D =100A, V _{GS} =10V		-	62		nC
Gate-Drain Charge	Q _{gd}			-	73		nC
Drain-Source Diode Characteristics						11	
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =100A		-		1.2	V
Diode Forward Current (Note 2)	I _S			-	-	200	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =	: 100A	-	101	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)		-	280	-	nC
		l					

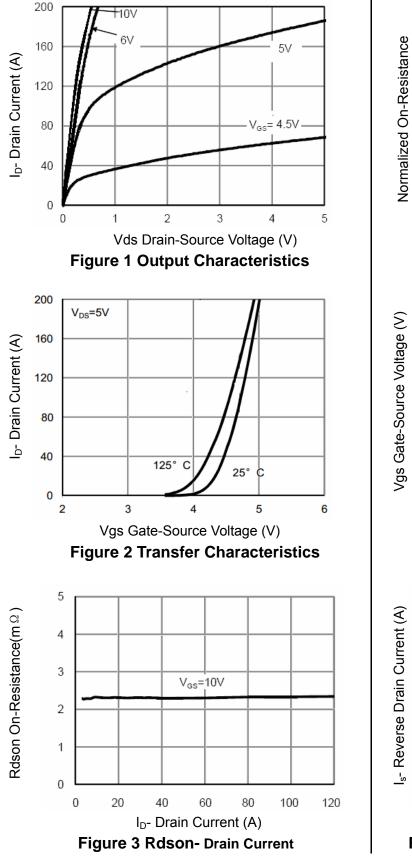
Notes:

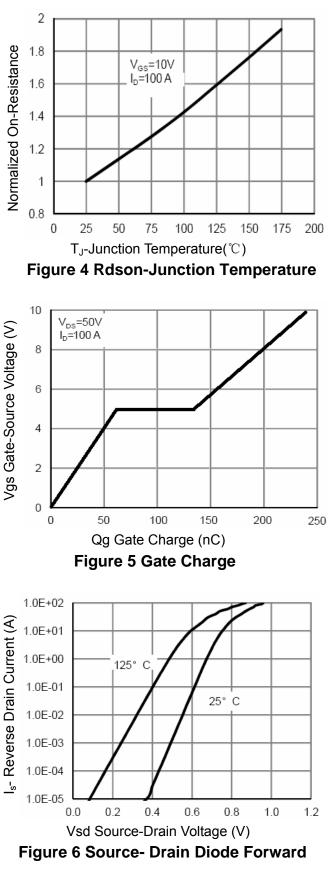
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300 μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^\circ \! \mathrm{C}$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25 Ω

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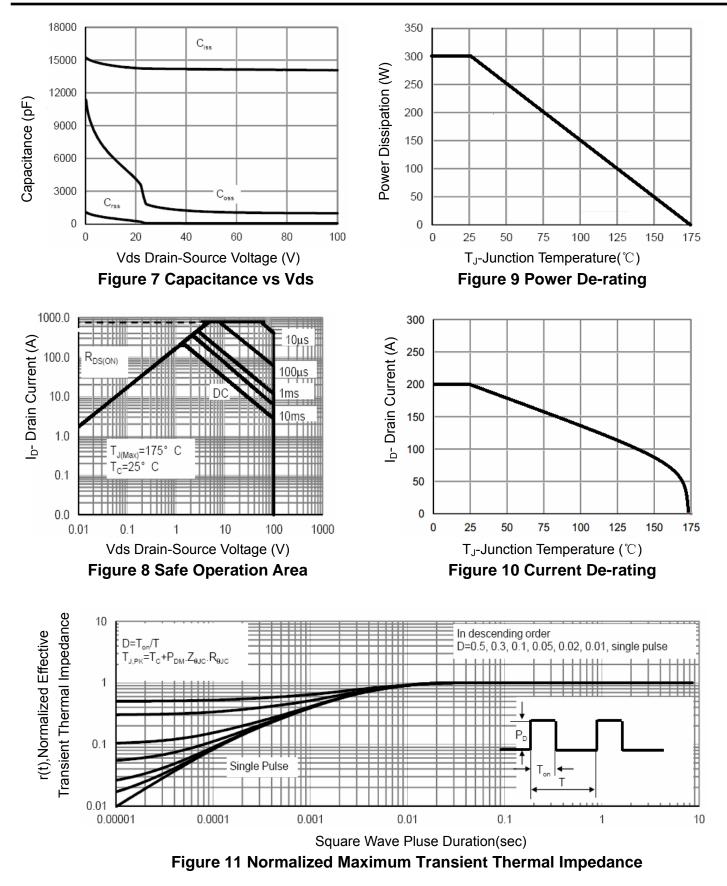






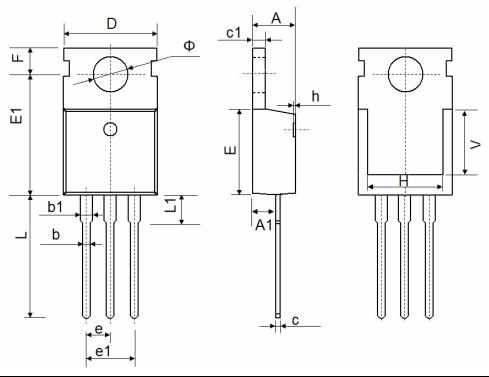


NCEP026N10, NCEP026N10D





TO-220-3L Package Information

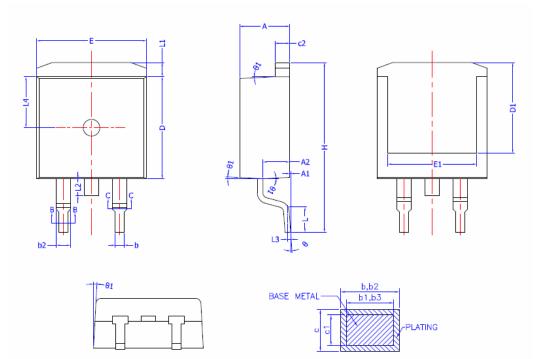


Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	6.900 REF.		0.276 REF.		
Φ	3.400	3.800	0.134	0.150	

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TO-263-2L Package Information



COMMON DIMENSIONS (UNITS OF MEASURE =MILLIMETER)

SECTION B-B&C-C

(UNITS OF MEASURE -MILLIMETER)						
SYMBOL	MIN	NOM	MAX			
Α	4.40	4.50	4.60			
A1	0	0.10	0.25			
A2	2,20	2,40	2,60			
b	0,76		0,89			
b1	0,75	0,80	0,85			
b2	1,23		1,37			
b3	1,22	1,27	1,32			
с	0,47		0,60			
c1	0,46	0,51	0.56			
c2	1,25	1,30	1,35			
D	9,10	9,20	9.30			
D1	8,00		—			
E	9,80	9,90	10.00			
E1	7.80	—	—			
е	2.54 BSC					
Н	14,90	15,30	15.70			
L	2.00	2,30	2.60			
L1	1.17	1.27	1.40			
L2			1,75			
L3	0.25BSC					
L4	4.60 REF					
θ	0°		8°			
θ1	1°	3°	5°			



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